



PJQ4476AP-AU

100V N-Channel Enhancement Mode MOSFET

Voltage

100 V

Current

35 A

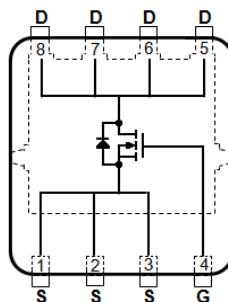
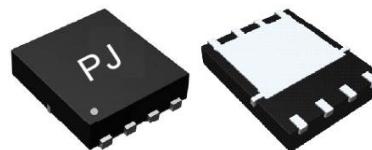
Features

- $R_{DS(ON)}$, $V_{GS} @ 10V$, $I_D @ 15A < 25m\Omega$
- $R_{DS(ON)}$, $V_{GS} @ 4.5V$, $I_D @ 10A < 28.5m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : DFN3333-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.001 ounces, 0.03 grams

DFN3333-8L



Maximum Ratings and Thermal Characteristics ($T_A = 25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current (^{Note 4})	I_D	35	A
$T_C = 100^\circ C$		22	
Pulsed Drain Current (^{Note 1})	I_{DM}	140	
Power Dissipation	P_D	62	W
$T_C = 100^\circ C$		25	
Continuous Drain Current (^{Note 4})	I_D	6.3	A
$T_A = 70^\circ C$		5	
Power Dissipation	P_D	2.0	W
$T_A = 70^\circ C$		1.3	
Single Pulse Avalanche Energy (^{Note 6})	E_{AS}	54	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~150	°C
Typical Thermal Resistance (^{Note 4,5})	Junction to Case	$R_{\theta JC}$	°C/W
	Junction to Ambient	$R_{\theta JA}$	
		2	
		62.5	



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Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.73	2.5	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=15A$	-	20	25	$m\Omega$
		$V_{GS}=4.5V, I_D=10A$	-	22	28.5	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V$	-	-	1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Dynamic <small>(Note 5)</small>						
Total Gate Charge	Q_g	$V_{DS}=50V, I_D=10A,$ $V_{GS}=10V$ <small>(Note 2,3)</small>	-	31	-	nC
Gate-Source Charge	Q_{gs}		-	5.1	-	
Gate-Drain Charge	Q_{gd}		-	7.3	-	
Input Capacitance	C_{iss}	$V_{DS}=30V, V_{GS}=0V,$ $f=1MHz$	-	1519	-	pF
Output Capacitance	C_{oss}		-	132	-	
Reverse Transfer Capacitance	C_{rss}		-	66	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=50V, I_D=10A,$ $V_{GS}=10V,$ $R_G=3\Omega$ <small>(Note 2,3)</small>	-	11	-	ns
Turn-On Rise Time	t_r		-	42	-	
Turn-Off Delay Time	$t_{d(off)}$		-	40	-	
Turn-Off Fall Time	t_f		-	19	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_s	---	-	-	35	A
Reverse Recovery Time	V_{SD}	$I_s=1A, V_{GS}=0V$	-	0.68	1.2	V

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ C$. Ratings are based on low frequency and duty cycles to keep initial $T_J = 25^\circ C$.
4. The maximum current rating is package limited.
5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
6. The test condition is $L=3mH, I_{AS}=6A, V_{DD}=50V, V_{GS}=10V$, Starting $T_J=25^\circ C$.
7. Guaranteed by design, not subject to production testing.



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TYPICAL CHARACTERISTIC CURVES

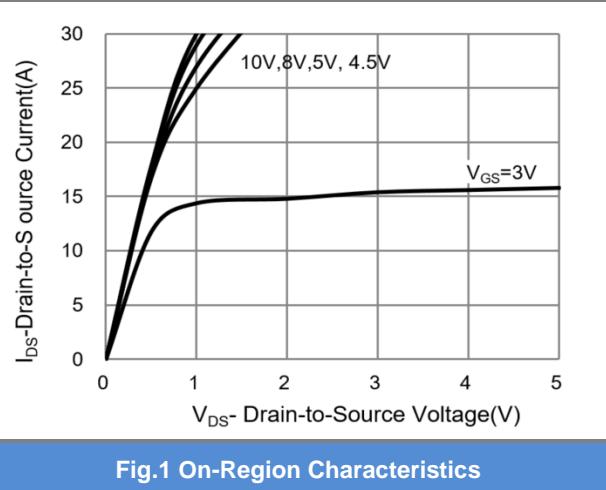


Fig.1 On-Region Characteristics

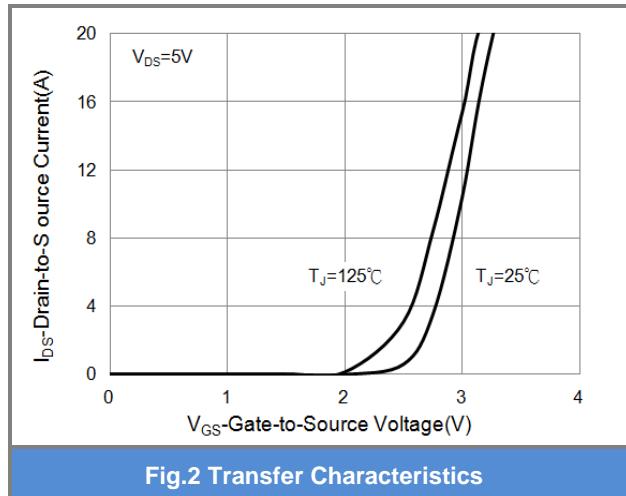


Fig.2 Transfer Characteristics

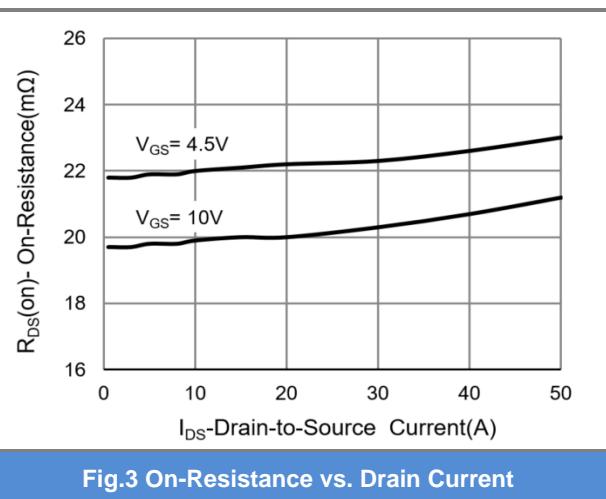


Fig.3 On-Resistance vs. Drain Current

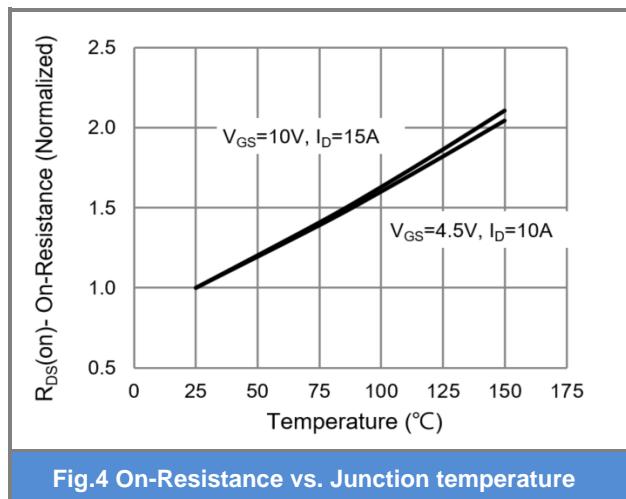


Fig.4 On-Resistance vs. Junction temperature

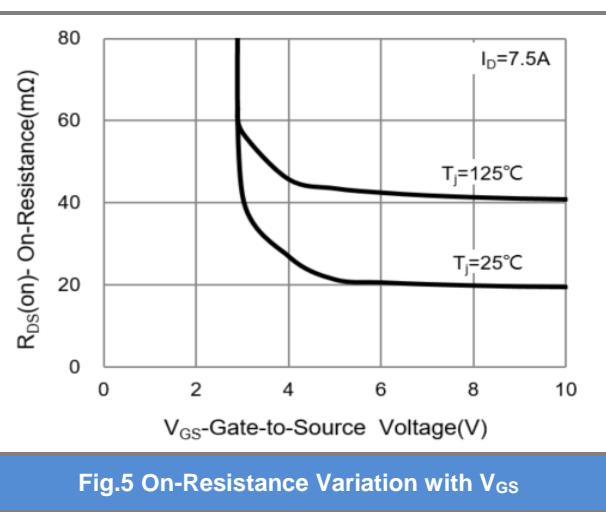


Fig.5 On-Resistance Variation with V_G

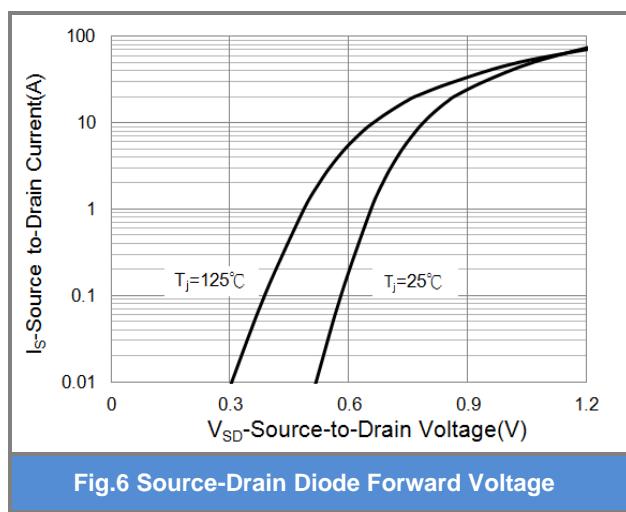


Fig.6 Source-Drain Diode Forward Voltage



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TYPICAL CHARACTERISTIC CURVES

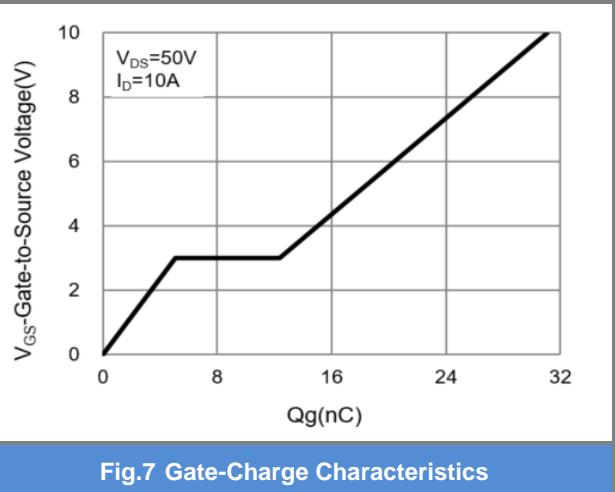


Fig.7 Gate-Charge Characteristics

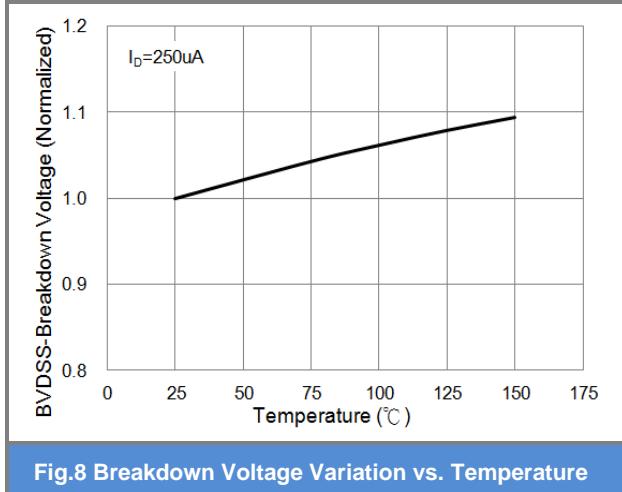


Fig.8 Breakdown Voltage Variation vs. Temperature

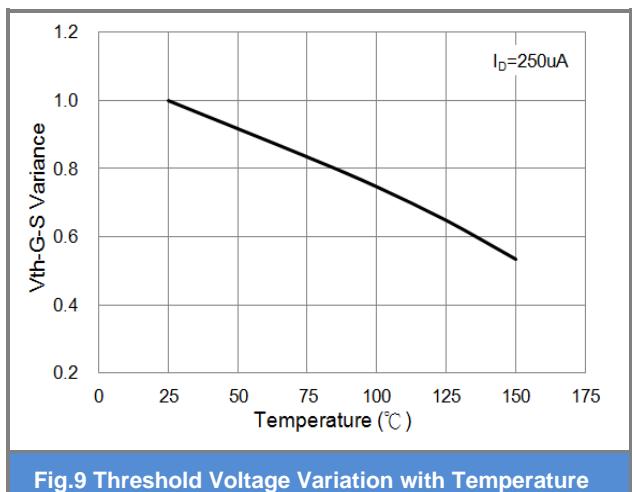


Fig.9 Threshold Voltage Variation with Temperature

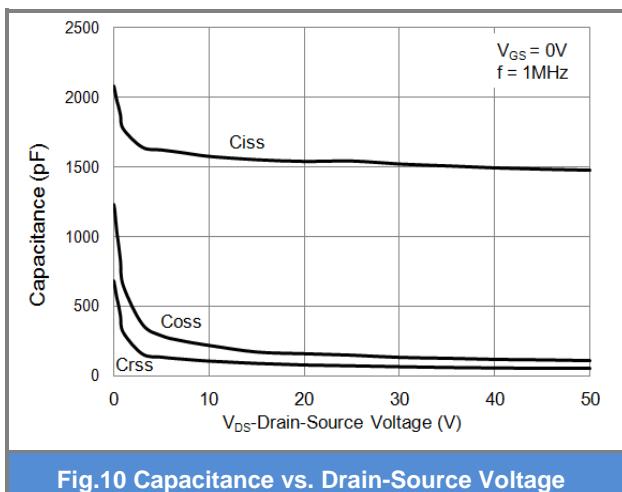


Fig.10 Capacitance vs. Drain-Source Voltage

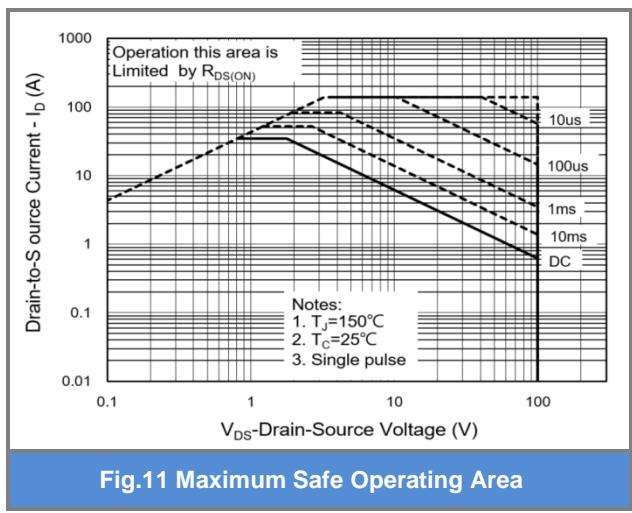


Fig.11 Maximum Safe Operating Area

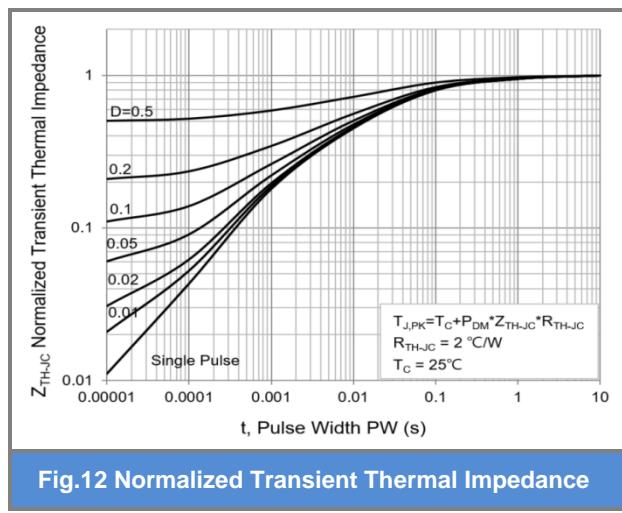


Fig.12 Normalized Transient Thermal Impedance

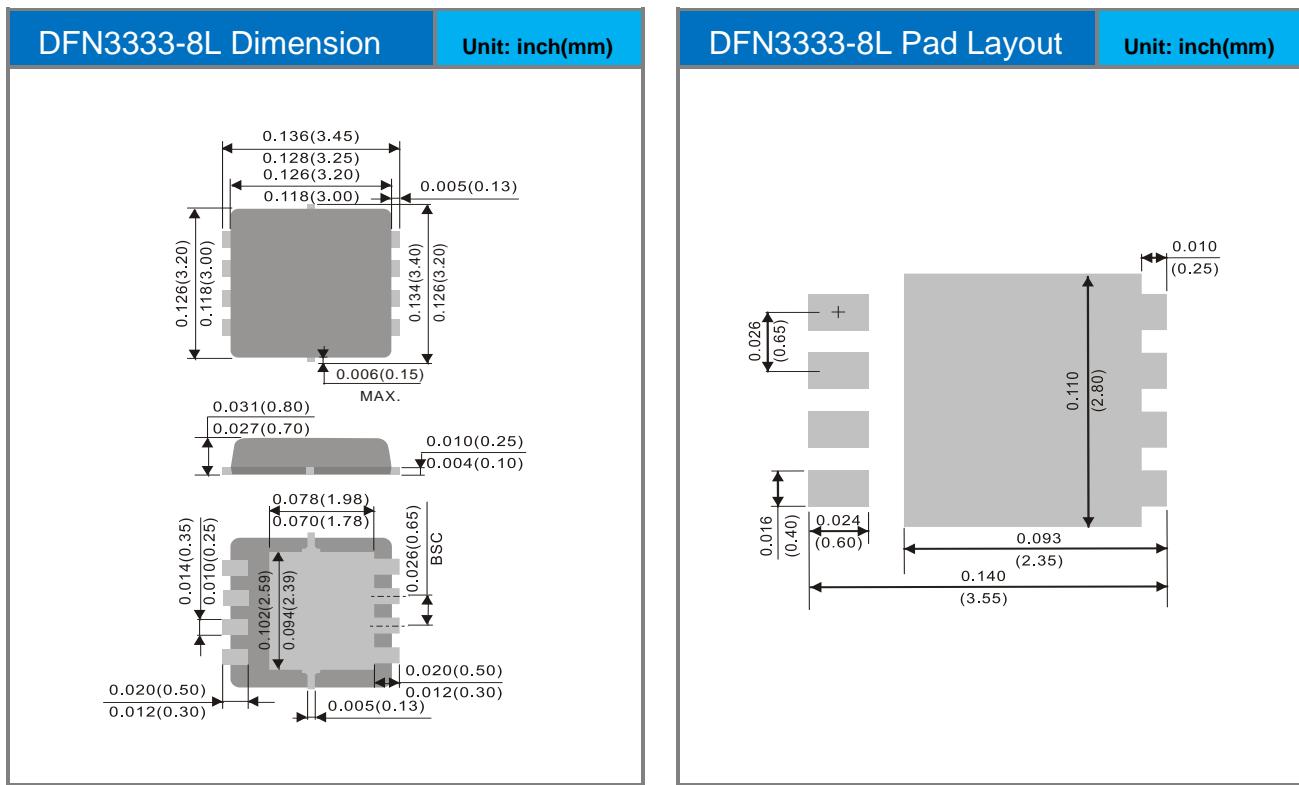


PJQ4476AP-AU

Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ4476AP-AU_R2_000A1	DFN3333-8L	5K pcs / 13" reel	4476	Halogen free

Packaging Information & Mounting Pad Layout





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